



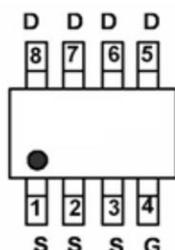
### General Features

- $V_{DS} = 60V, I_D = 9A$
- $R_{DS(ON)} < 18m\Omega @ V_{GS}=10V$  (Typ:12mΩ)

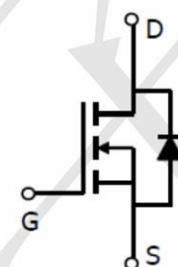
### Application

- High power and current handing capability
- Lead free product is acquired
- Surface mount package

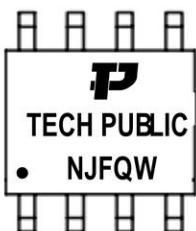
### Package and Pin Configuration



Circuit diagram



### Marking



### Absolute Maximum Ratings ( $T_c=25^\circ C$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	$V_{DS}$	60	V
Gate-Source Voltage	$V_{GS}$	$\pm 20$	V
Drain Current-Continuous	$I_D$	9	A
Drain Current-Continuous( $T_c=100^\circ C$ )	$I_D(100^\circ C)$	6.4	A
Pulsed Drain Current	$I_{DM}$	36	A
Maximum Power Dissipation	$P_D$	2.6	W
Operating Junction and Storage Temperature Range	$T_J, T_{STG}$	-55 To 150	°C

### Thermal Characteristic

Thermal Resistance, Junction-to-Ambient <sup>(Note 2)</sup>	$R_{\theta JA}$	48	°C/W
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**AO4266**

N-Channel Enhancement Mode Power MOSFET

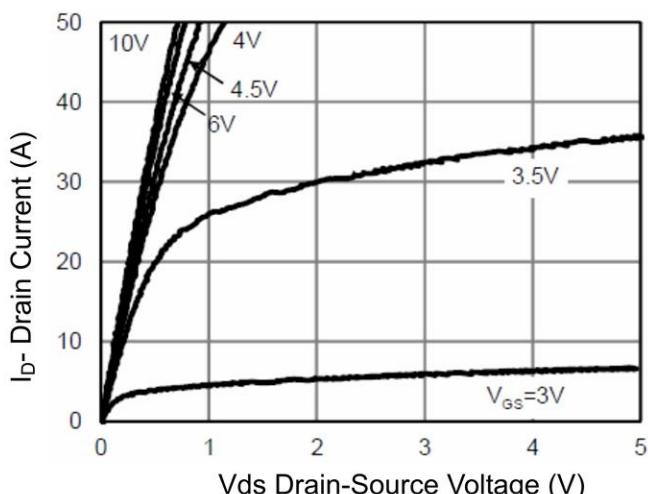
[www.sot23.com.tw](http://www.sot23.com.tw)

**Electrical Characteristics (TC=25°C unless otherwise noted)**

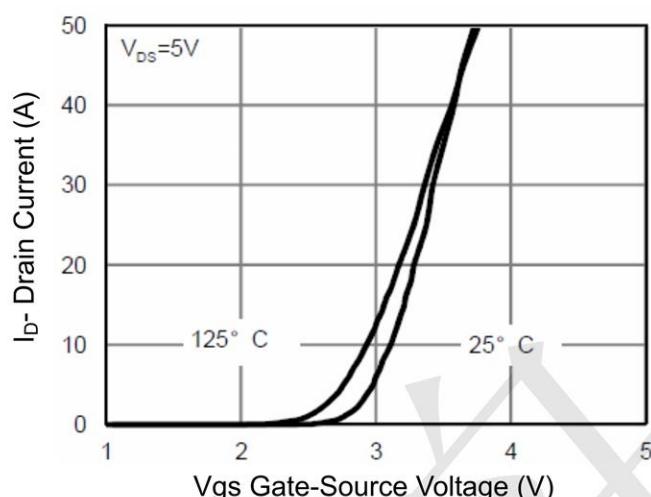
Parameter	Symbol	Condition	Min	Typ	Max	Unit
<b>Off Characteristics</b>						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V, I <sub>D</sub> =250μA	60	-	-	V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =60V, V <sub>GS</sub> =0V	-	-	1	μA
Gate-Body Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> =±20V, V <sub>DS</sub> =0V	-	-	±100	nA
<b>On Characteristics</b> <sup>(Note 3)</sup>						
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250μA	1.2	1.8	2.2	V
Drain-Source On-State Resistance	R <sub>D(S)ON</sub>	V <sub>GS</sub> =10V, I <sub>D</sub> =9A	-	12	18	mΩ
Forward Transconductance	g <sub>FS</sub>	V <sub>DS</sub> =5V, I <sub>D</sub> =9A	25	-	-	S
<b>Dynamic Characteristics</b> <sup>(Note 4)</sup>						
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> =30V, V <sub>GS</sub> =0V, F=1.0MHz	-	2180	-	PF
Output Capacitance	C <sub>oss</sub>		-	350	-	PF
Reverse Transfer Capacitance	C <sub>rss</sub>		-	270	-	PF
<b>Switching Characteristics</b> <sup>(Note 4)</sup>						
Turn-on Delay Time	t <sub>d(on)</sub>	V <sub>DD</sub> =30V, R <sub>L</sub> =1Ω V <sub>GS</sub> =10V, R <sub>GEN</sub> =3Ω	-	8.5	-	nS
Turn-on Rise Time	t <sub>r</sub>		-	6	-	nS
Turn-Off Delay Time	t <sub>d(off)</sub>		-	30	-	nS
Turn-Off Fall Time	t <sub>f</sub>		-	5	-	nS
Total Gate Charge	Q <sub>g</sub>	V <sub>DS</sub> =30V, I <sub>D</sub> =8A, V <sub>GS</sub> =10V	-	58	-	nC
Gate-Source Charge	Q <sub>gs</sub>		-	8	-	nC
Gate-Drain Charge	Q <sub>gd</sub>		-	17	-	nC
<b>Drain-Source Diode Characteristics</b>						
Diode Forward Voltage <sup>(Note 3)</sup>	V <sub>SD</sub>	V <sub>GS</sub> =0V, I <sub>S</sub> =9A	-	-	1.2	V
Diode Forward Current <sup>(Note 2)</sup>	I <sub>S</sub>	-	-	-	9	A
Reverse Recovery Time	t <sub>rr</sub>	T <sub>J</sub> = 25°C, IF=9A di/dt = 100A/μs <sup>(Note 3)</sup>	-	30	-	nS
Reverse Recovery Charge	Q <sub>rr</sub>		-	44	-	nC



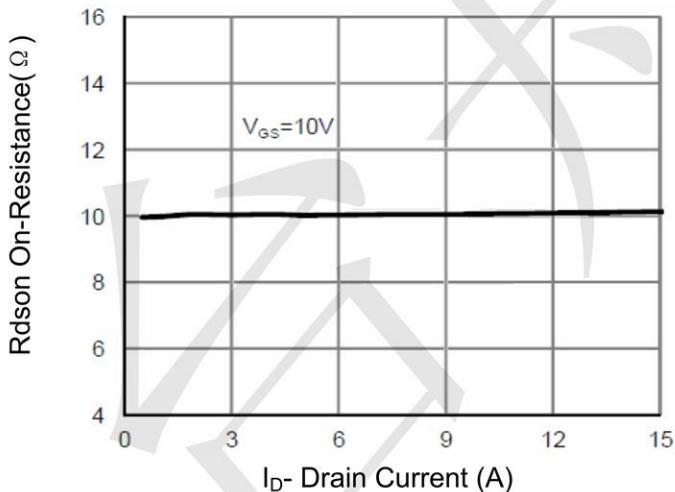
### Typical Electrical and Thermal Characteristics



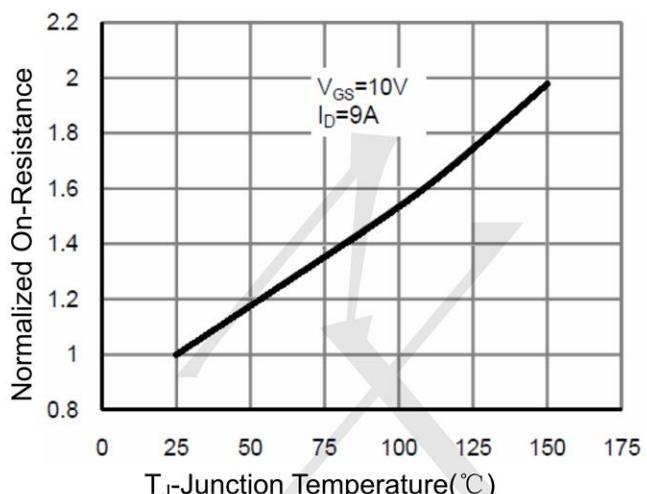
**Figure 1 Output Characteristics**



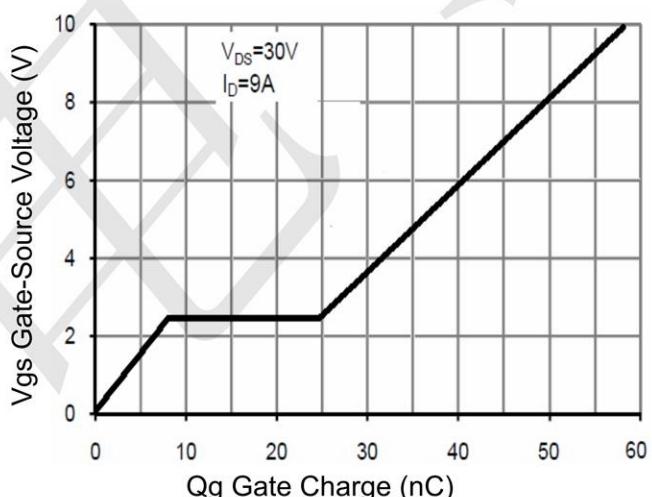
**Figure 2 Transfer Characteristics**



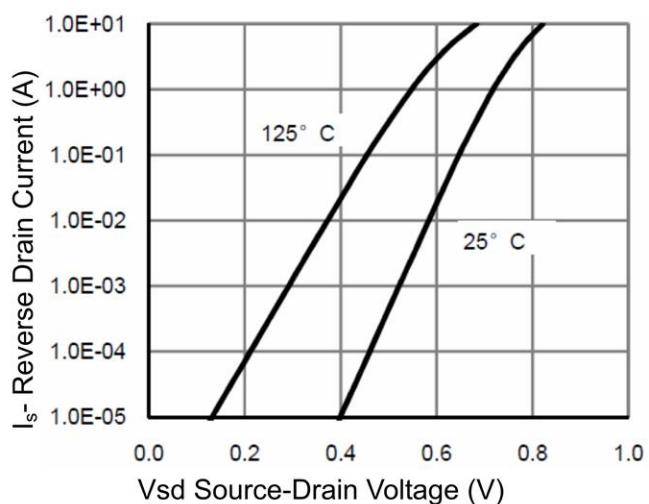
**Figure 3 Rdson- Drain Current**



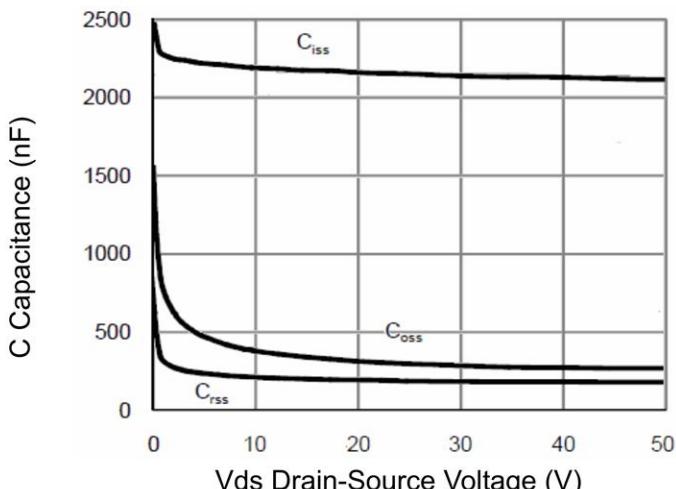
**Figure 4 Rdson-JunctionTemperature**



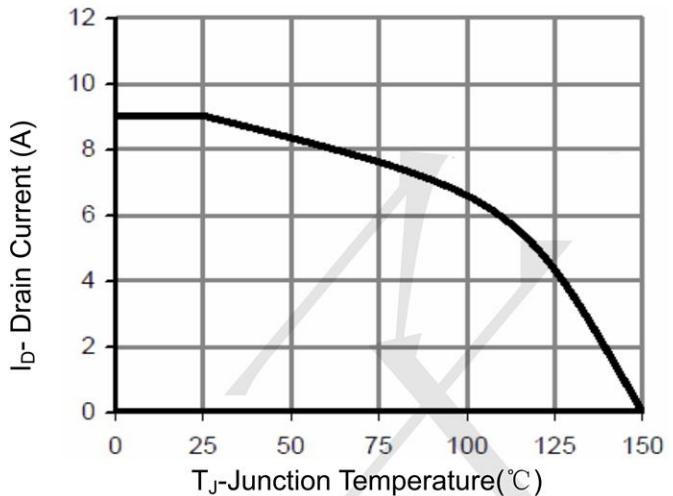
**Figure 5 Gate Charge**



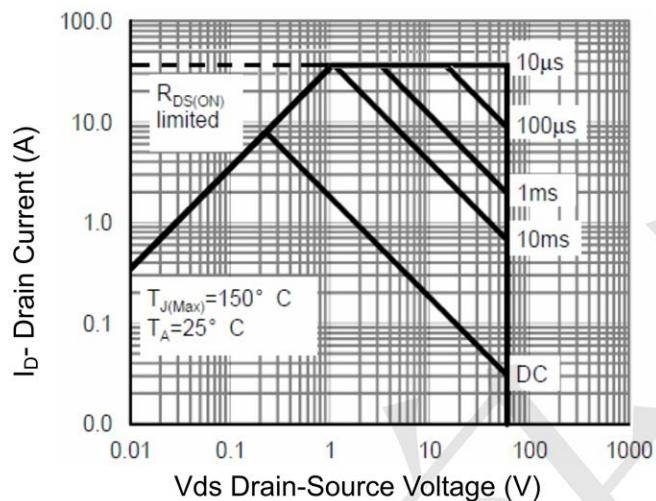
**Figure 6 Source- Drain Diode Forward**



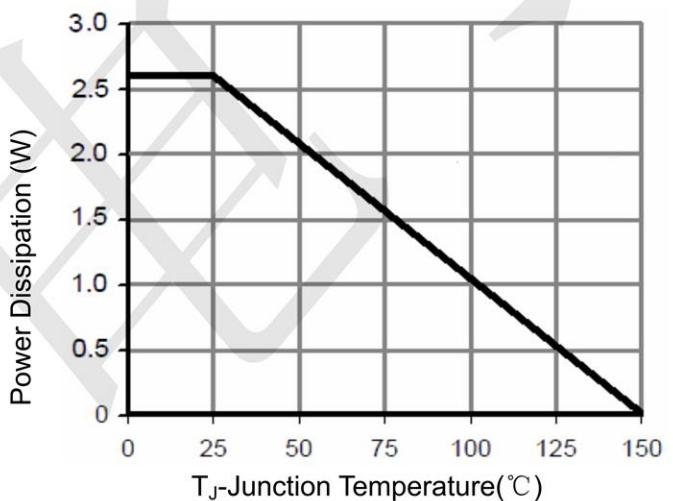
**Figure 7 Capacitance vs Vds**



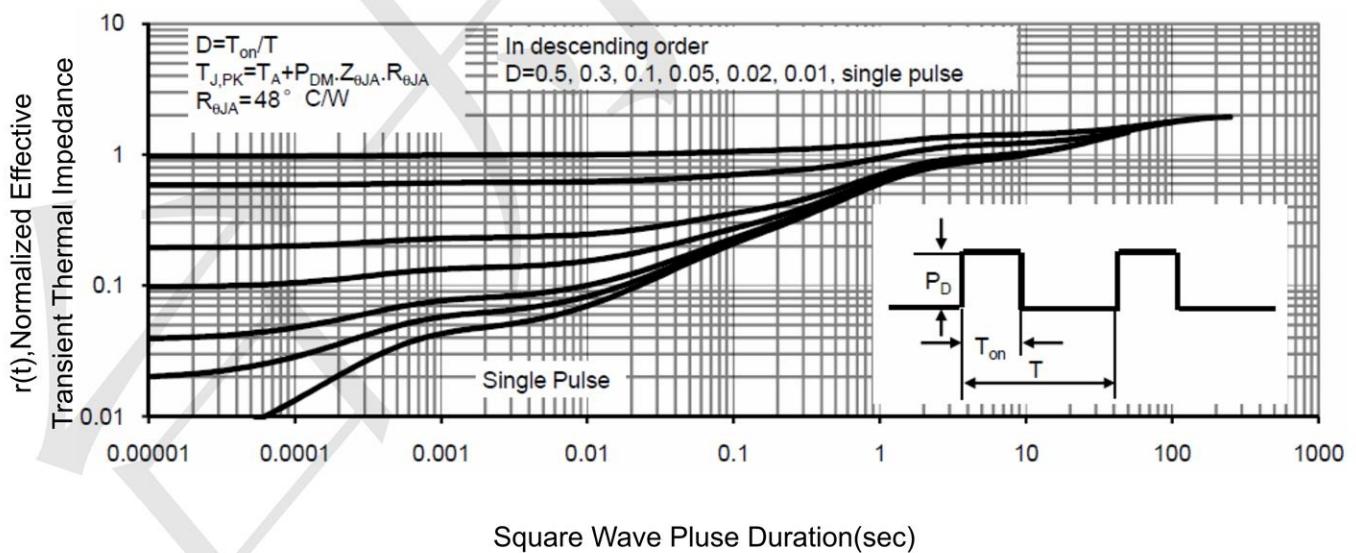
**Figure 9 Current De-rating**



**Figure 8 Safe Operation Area**



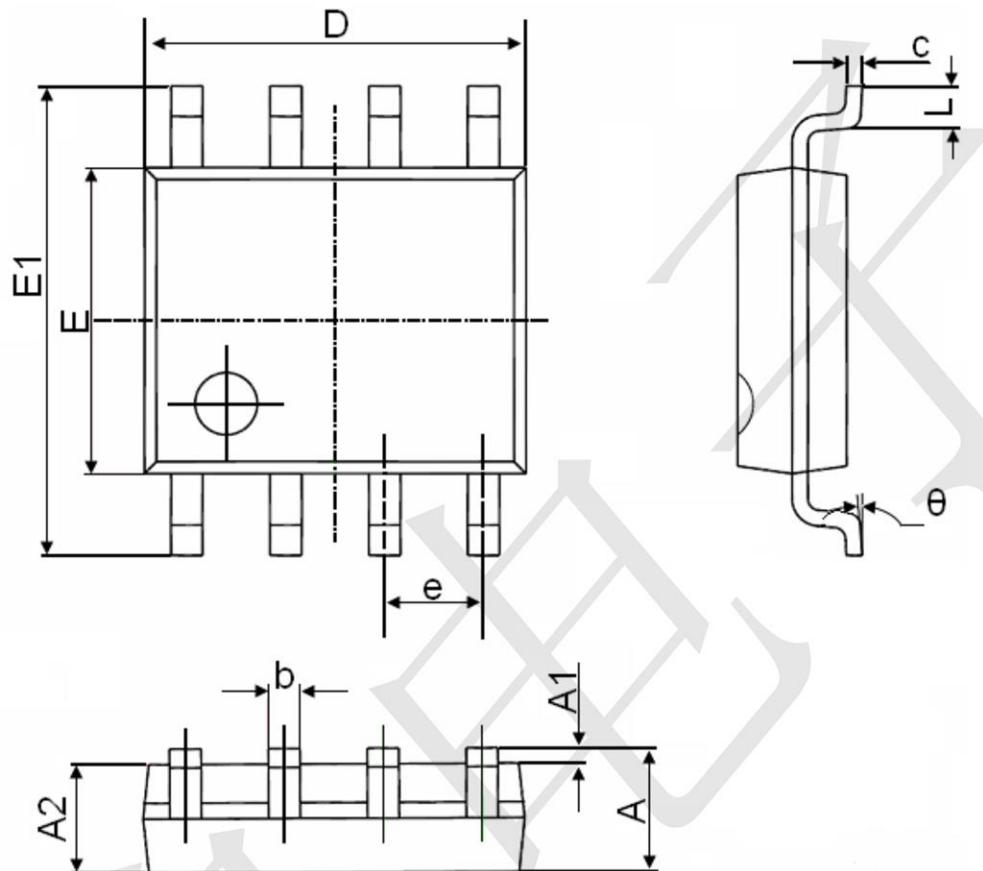
**Figure 10 Power De-rating**



**Figure 11 Normalized Maximum Transient Thermal Impedance**



**SOP-8 Package Information**



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	1.350	1.750	0.053	0.069
A1	0.100	0.250	0.004	0.010
A2	1.350	1.550	0.053	0.061
b	0.330	0.510	0.013	0.020
c	0.170	0.250	0.006	0.010
D	4.700	5.100	0.185	0.200
E	3.800	4.000	0.150	0.157
E1	5.800	6.200	0.228	0.244
e	1.270(BSC)		0.050(BSC)	
L	0.400	1.270	0.016	0.050
θ	0°	8°	0°	8°

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